

General Description

The WSP4435A is the highest performance trench P-Ch MOSFET with extreme high cell density , which provide excellent R_{DSON} and gate charge for most of the synchronous buck converter applications .

The WSP4435A meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

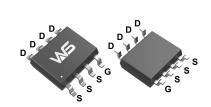
Product Summery

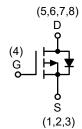
| BV _{DSS} | R _{DSON} | I _D |
|-------------------|-------------------|----------------|
| -30V | 20mΩ | -8A |

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOP-8L Pin Configuration





Absolute Maximum Ratings

| Symbol | Parameter | Rating | Units |
|--------------------------------------|---|------------|------------|
| V_{DS} | Drain-Source Voltage | -30 | V |
| V_{GS} | Gate-Source Voltage | ±20 | V |
| I _D @T _C =25℃ | Continuous Drain Current, V _{GS} @ -10V ¹ | -8 | Α |
| I _D @T _C =70℃ | Continuous Drain Current, V _{GS} @ -10V ¹ | -6.5 | А |
| I _{DM} | Pulsed Drain Current ² | -32 | Α |
| EAS | Single Pulse Avalanche Energy ³ | 64 | mJ |
| I _{AS} | Avalanche Current | -16 | Α |
| P _D @T _A =25°C | Total Power Dissipation⁴ | 2.0 | W |
| T _{STG} | Storage Temperature Range | -55 to 150 | $^{\circ}$ |
| TJ | Operating Junction Temperature Range -55 to 150 | | $^{\circ}$ |

Thermal Data

| Symbol | Parameter | | Max. | Unit |
|----------------|--|--|------|------|
| $R_{	heta JA}$ | Thermal Resistance Junction-Ambient ¹ | | 90 | °C/W |
| $R_{	heta JC}$ | Thermal Resistance Junction-Case ¹ | | 50 | °C/W |



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

| Symbol | Parameter | Conditions | Min. | Тур. | Max. | Unit |
|--------------------------------------|--|--|------|--------|------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V_{GS} =0V , I_D =-250uA | -30 | | | V |
| $\triangle BV_{DSS}/\triangle T_{J}$ | BV _{DSS} Temperature Coefficient | Reference to 25℃, I _D =-1mA | | -0.022 | | V/°C |
| В | Static Drain-Source On-Resistance ² | V_{GS} =-10V , I_D =-8.2A | | 20 | 23 | mΩ |
| $R_{DS(ON)}$ | Static Drain-Source On-Resistance | V _{GS} =-4.5V , I _D =-4A | | 25 | 33 | |
| $V_{GS(th)}$ | Gate Threshold Voltage | V _{GS} =V _{DS} . I _D =-250uA | -1.5 | -2.0 | -2.5 | ٧ |
| $\triangle V_{GS(th)}$ | V _{GS(th)} Temperature Coefficient | V _{GS} -V _{DS} , I _D 230uA | | 4.6 | | mV/℃ |
| | Drain Source Lookage Current | V_{DS} =-24V , V_{GS} =0V , T_J =25 $^{\circ}$ C | | | -1 | uA |
| I _{DSS} | Drain-Source Leakage Current | V_{DS} =-24V , V_{GS} =0V , T_J =55 $^{\circ}$ C | | | -5 | uA |
| I _{GSS} | Gate-Source Leakage Current | V_{GS} = $\pm 20 V$, V_{DS} = $0 V$ | | | ±100 | nA |
| gfs | Forward Transconductance | V_{DS} =-5V , I_D =-6A | | 11 | | S |
| R_g | Gate Resistance | V_{DS} =0V , V_{GS} =0V , f=1MHz | | 3 | | Ω |
| Q_g | Total Gate Charge (-4.5V) | | | 21 | | |
| Q_{gs} | Gate-Source Charge | V _{DS} =-15V , V _{GS} =-4.5V , I _D =-8.2A | | 2.6 | | nC |
| Q_{gd} | Gate-Drain Charge | | | 6.2 | | |
| T _{d(on)} | Turn-On Delay Time | | | 8 | | |
| T _r | Rise Time | V_{DD} =-15V , V_{GS} =-10V , R_{G} =6 Ω , | | 12 | | no |
| T _{d(off)} | Turn-Off Delay Time | I _D =-6A ,R _L =15Ω, | | 16 | | ns |
| T _f | Fall Time | | | 32 | | |
| C _{iss} | Input Capacitance | | | 1000 | | |
| C _{oss} | Output Capacitance | ance V _{DS} =-15V , V _{GS} =0V , f=1MHz | | 210 | | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 150 | | |

Guaranteed Avalanche Characteristics

| Symbol | Parameter | Conditions | Min. | Тур. | Max. | Unit |
|--------|--|---|------|------|------|------|
| EAS | Single Pulse Avalanche Energy ⁵ | V _{DD} =-25V , L=0.5mH , I _{AS} =-16A | 49 | | | mJ |

Diode Characteristics

| Symbol | Parameter Conditions | | Min. | Тур. | Max. | Unit |
|-----------------|--|---|------|------|------|------|
| Is | Continuous Source Current ^{1,6} | V =V =0V Force Current | | | -2.0 | Α |
| I _{SM} | Pulsed Source Current ^{2,6} | V _G =V _D =0V , Force Current | | | -32 | Α |
| V _{SD} | Diode Forward Voltage ² | V _{GS} =0V , I _S =-1A , T _J =25℃ | | | -1.2 | V |
| t _{rr} | Reverse Recovery Time | I- 04 II/II 4004/ T 05°C | | 16.3 | | nS |
| Q _{rr} | Reverse Recovery Charge | IF=-8A , dl/dt=100A/μs , T _J =25℃ | | 5.9 | | nC |

Note:

- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, t<10 sec.
- 2.The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%
- 3. The EAS data shows Max. rating . The test condition is V_{DD} =-25V, V_{GS} =-10V,L=0.5mH,I_{AS}=-16A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The Min. value is 100% EAS tested guarantee.
- 6. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



Typical Characteristics

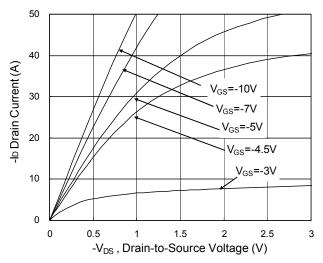


Fig.1 Typical Output Characteristics

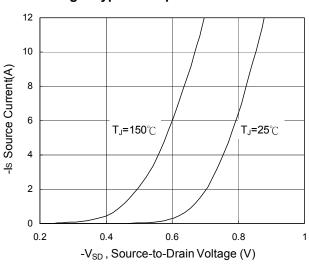


Fig.3 Forward Characteristics of Reverse

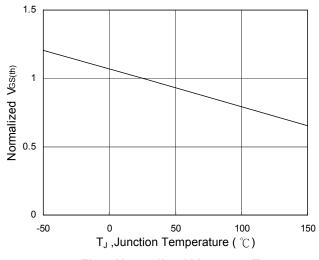


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

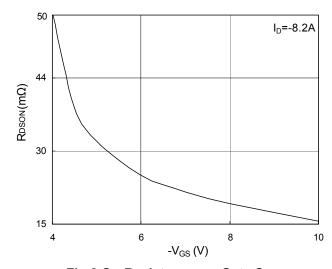


Fig.2 On-Resistance v.s Gate-Source

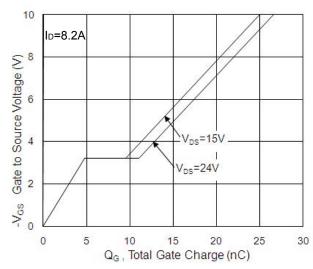


Fig.4 Gate-Charge Characteristics

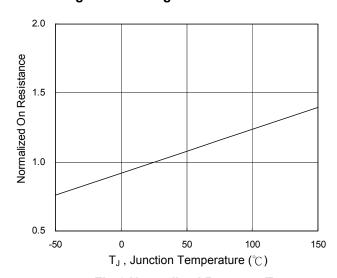
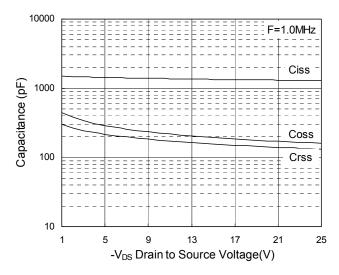


Fig.6 Normalized R_{DSON} vs. T_J





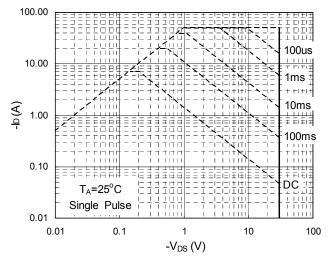


Fig.7 Capacitance

Fig.8 Safe Operating Area

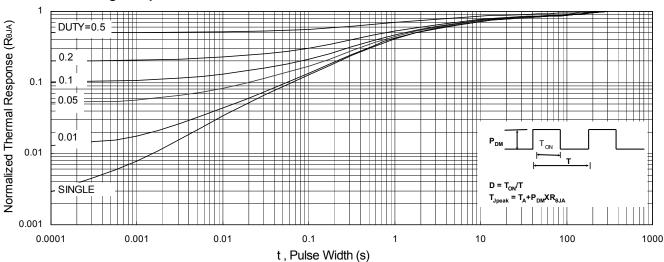


Fig.9 Normalized Maximum Transient Thermal Impedance

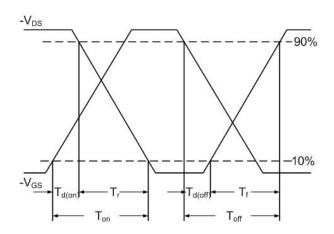


Fig.10 Switching Time Waveform

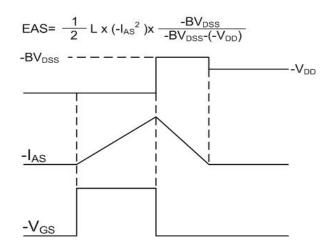
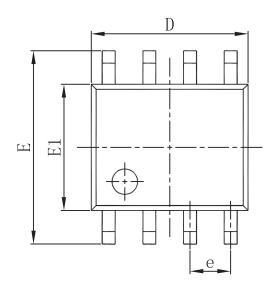
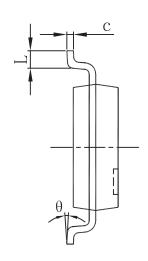


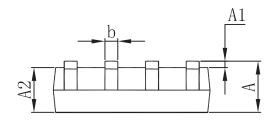
Fig.11 Unclamped Inductive Switching Waveform



Packaging information







| Completel | Dimensions In Millimeters | | Dimensions | In Inches |
|-----------|---------------------------|--------|-------------|-----------|
| Symbol | Min | Max | Min | Max |
| A | 1. 350 | 1.750 | 0.053 | 0.069 |
| A1 | 0. 100 | 0. 250 | 0.004 | 0.010 |
| A2 | 1. 350 | 1. 550 | 0. 053 | 0.061 |
| b | 0. 330 | 0. 510 | 0. 013 | 0. 020 |
| С | 0. 170 | 0. 250 | 0.007 | 0.010 |
| D | 4.800 | 5. 000 | 0. 189 | 0. 197 |
| e | 1.270 (BSC) | | 0.050 (BSC) | |
| Е | 5. 800 | 6. 200 | 0. 228 | 0. 244 |
| E1 | 3. 800 | 4. 000 | 0. 150 | 0. 157 |
| L | 0.400 | 1. 270 | 0.016 | 0.050 |
| θ | 0° | 8° | 0° | 8° |



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